



F18NM70

Preliminary

Power MOSFET

18A, 700V N-CHANNEL SUPER-JUNCTION MOSFET

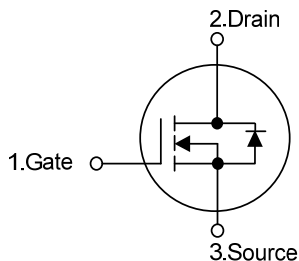
DESCRIPTION

The **UTC F18NM70** is a N-Channel enhancement mode silicon gate super junction power MOSFET with fast body diode and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 0.35 \Omega @ V_{GS}=10V, I_D=9.0A$
- * Fast body diode MOSFET technology
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL

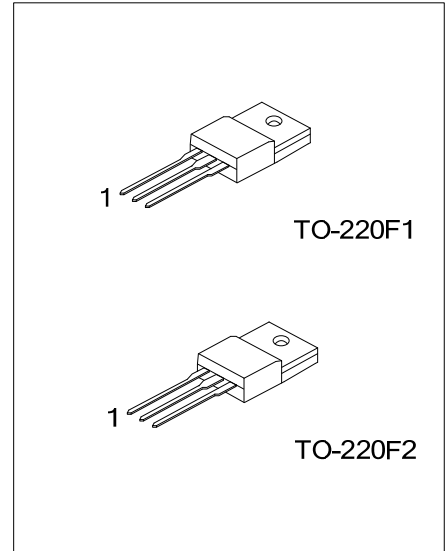


ORDERING INFORMATION

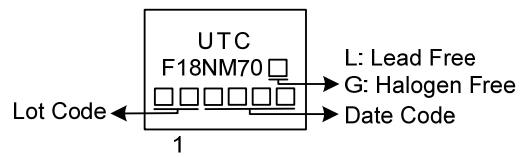
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
F18NM70L-TF1-T	F18NM70G-TF1-T	TO-220F1	G	D	S	Tube
F18NM70L-TF2-T	F18NM70G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>F18NM70G-TF1-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) TF1: TO-220F1, TF2: TO-220F2 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I_D	18	A
Pulsed Drain Current (Note 2)		I_{DM}	36	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	480	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	12	V/ns
Power Dissipation		P_D	33	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 100\text{mH}$, $I_{AS} = 3.1\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD} \leq 18\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	3.78	$^{\circ}\text{C}/\text{W}$

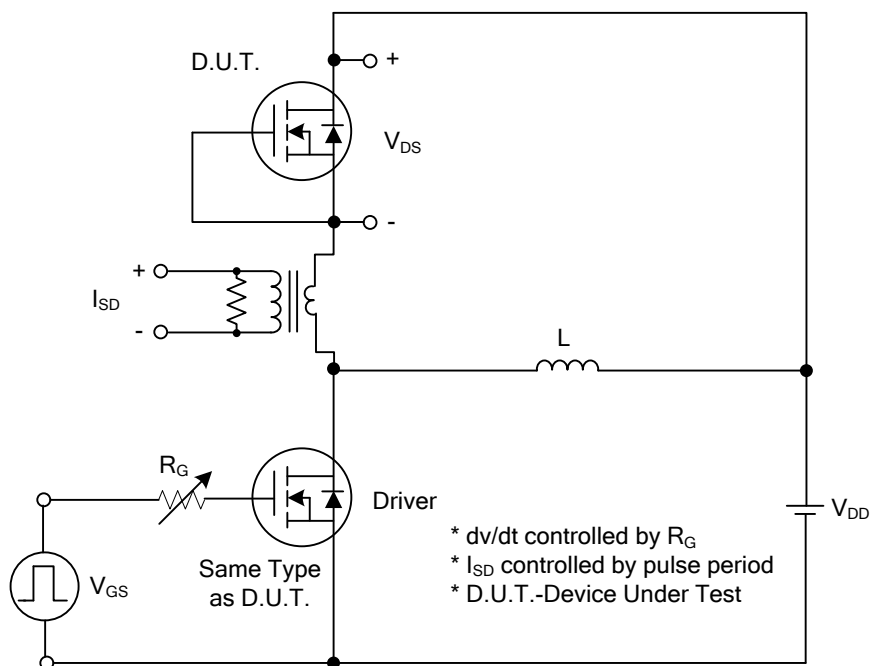
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	700			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =700V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =9.0A			0.35	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		1150		pF
Output Capacitance		C _{OSS}			670		pF
Reverse Transfer Capacitance		C _{RSS}			62		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =560V, V _{GS} =10V, I _D =18A I _G =1mA (Note 1, 2)		43		nC
Gate-Source Charge		Q _{GS}			10		nC
Gate-Drain Charge		Q _{GD}			15.6		nC
Turn-On Delay Time (Note 1)		t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =18A, R _G =25Ω (Note 1, 2)		17		ns
Turn-On Rise Time		t _R			26		ns
Turn-Off Delay Time		t _{D(OFF)}			122		ns
Turn-Off Fall Time		t _F			82		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Continuous Drain-Source Diode Forward Current		I _S				18	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				36	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =18A , V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =18A , V _{GS} =0V		145		ns
Reverse Recovery Charge		Q _{rr}	di/dt=100A/μs		1.65		μC

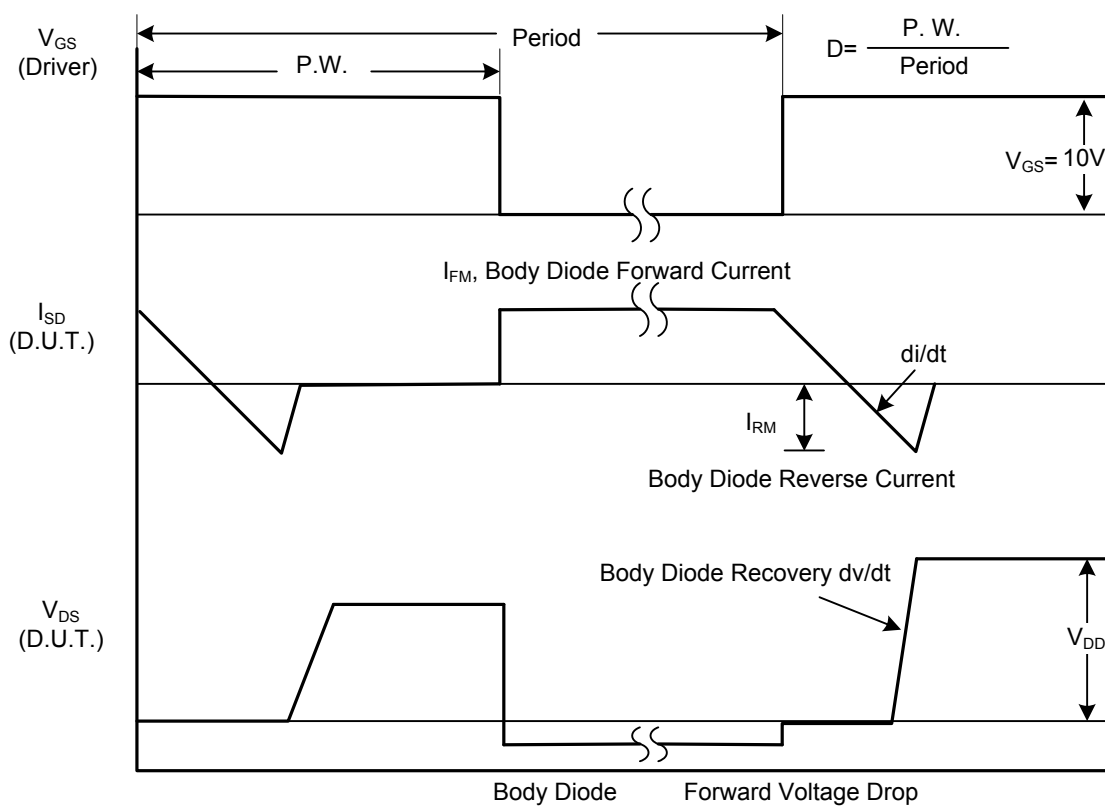
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

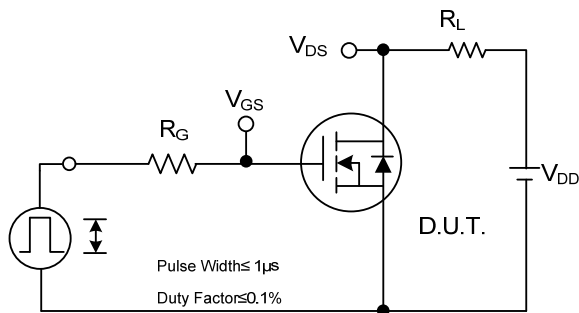


Peak Diode Recovery dv/dt Test Circuit

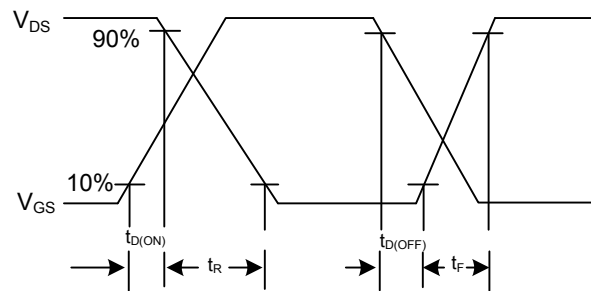


Peak Diode Recovery dv/dt Waveforms

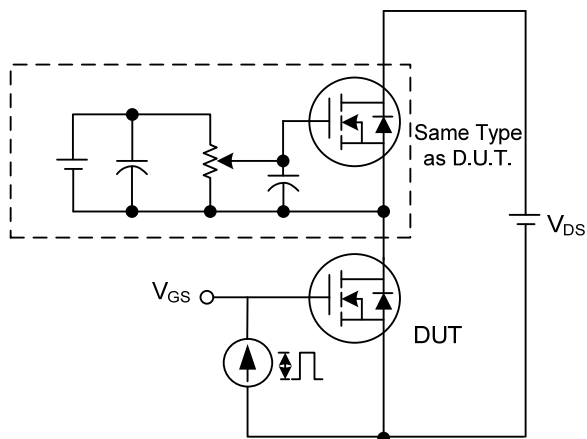
■ TEST CIRCUITS AND WAVEFORMS



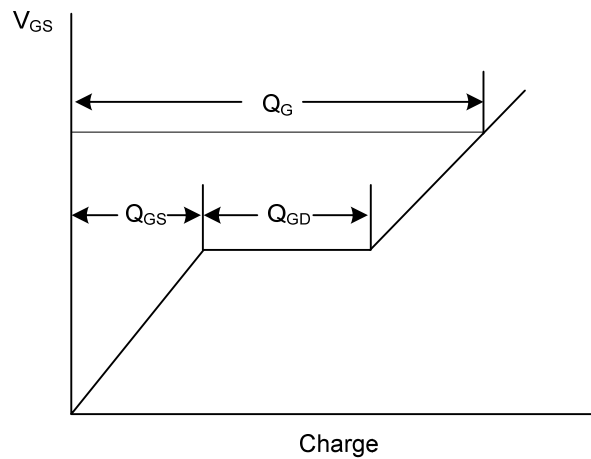
Switching Test Circuit



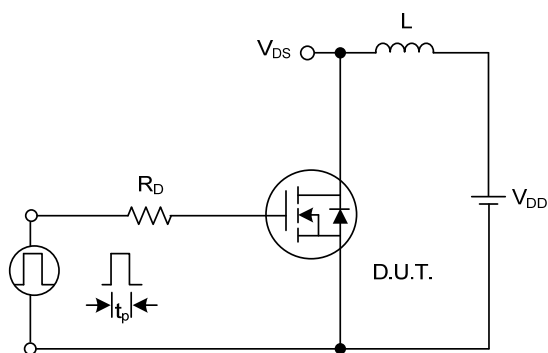
Switching Waveforms



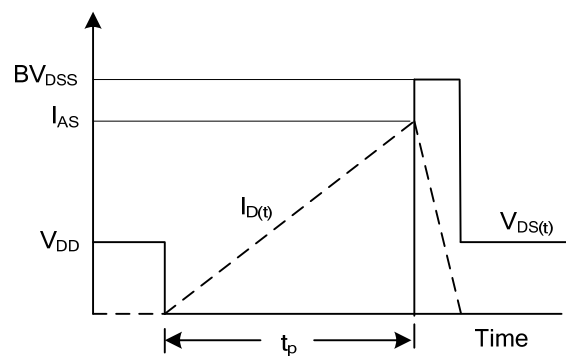
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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